Application No.: 09/497,508 Docket No.: 8733.213.00

REMARKS

At the outset, the Examiner is thanked for the thorough review and consideration of the pending application. The final Office Action dated April 20, 2005 has been received and its contents carefully reviewed.

By this Amendment, Applicants amend claim 9. Claims 14-19 are withdrawn from consideration due to an earlier constructive restriction requirement. Accordingly, Claims 9-19 are currently pending. Reexamination and reconsideration of the pending claims is respectfully requested.

In the Office Action, the Examiner rejected claims 9-13 under 35 U.S.C. § 112, first paragraph, as failing to comply with the written description requirement. Although Applicants respectfully disagree with the Examiner, for the sole purpose of expediting prosecution of this application, claim 9 has been amended. In view of this, Applicants respectfully request that this rejection be withdrawn.

In addition, the Examiner rejected claims 9-13 under 35 U.S.C. § 103(a) as being unpatentable over Miyanaga et al. (U.S. Patent No. 5,932,893) in view of Fonash et al. (U.S. Patent No. 5,994,164). This rejection is respectfully traversed and reconsideration is requested.

Claim 9 is allowable over the cited references in that claim 9 recites a combination of elements including, for example, "...wherein the polycrystalline silicon film is formed by crystallizing an amorphous silicon film containing the metal by a thermal treatment and applying an electric field." None of the cited references, singly or in combination, teaches or suggests at least this feature of the claimed invention. Accordingly, Applicants respectfully submit that claim 9 and claims 10-13, which depend therefrom, are allowable over the cited references.

On page 5 of the Office Action dated November 1, 2004, the Examiner states, "during operation of a lamp, a high-frequency electric field is generated..."

Applicants respectfully submit that in the present application, "annealing time is dramatically shortened and annealing temperature is greatly reduced in metal induced crystallization provided that electric field is applied to an amorphous silicon film containing metal." See the present application at page 6, lines 6-9. In contrast, Applicants respectfully

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submit that as best understood, electric field generated during operation of a lamp is negligible and incapable of affecting the crystallization.

Applicants believe the application is in condition for allowance and early, favorable action is respectfully solicited. If for any reason the Examiner finds the application other than in condition for allowance, the Examiner is requested to call the undersigned attorney at (202) 496-7500 to discuss the steps necessary for placing the application in condition for allowance. All correspondence should continue to be sent to the below-listed address.

If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. §1.136, and any additional fees required under 37 C.F.R. §1.136 for any necessary extension of time, or any other fees required to complete the filing of this response, may be charged to Deposit Account No. 50-0911. Please credit any overpayment to deposit Account No. 50-0911. A duplicate copy of this sheet is enclosed.

Dated: <u>August 22, 2005</u>

Respectfully submitted,

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